## 100Mbps / 155Mbps / 622Mbps

## Large Active Area and High Speed Silicon Photodiodes

OSI Optoelectronics's family of large active area and high speed silicon detector series are designed to reliably support short-haul data communications applications. All exhibit low dark current and low capacitance at 3.3V bias. The base unit comes in a 3 pin TO-46 package with micro lens cap or AR coated flat window. Standard fiber optic receptacles (FC, ST, SC and SMA) allow easy integration of OSI Optoelectronics's fast silicon photodiodes into systems.



## APPLICATIONS

- High Speed Optical Communications
- Single/Multi-Mode Fiber Optic Large Diameter Sensing Area Receiver
- Fast Ethernet/FDDI • SONET/SDH, ATM
- High Responsivity

Silicon Photodiodes

- Low Capacitance @ 3.3V Bias
- Low Cost

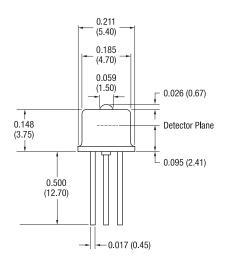
FEATURES

Absolute Maximum Ratings											
PARAMETERS	SYMBOL	MIN	МАХ	UNITS							
Storage Temperature	T <sub>stg</sub>	-55	+125	°C							
Operating Temperature	T <sub>op</sub>	-40	+75	°C							
Soldering Temperature	T <sub>sld</sub>		+260	°C							

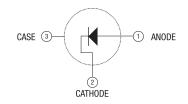
Electro-Optic	Electro-Optical Characteristics T <sub>A</sub> =23°C															23°C											
PARAMETERS	SYMBOL	CONDITIONS		FCI-HR005			FCI-HR008			FCI-HR020		FCI-HR026			FCI-HR040			UNITE									
				MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNITS								
Active Area Diameter	$AA_{\phi}$				127			203			508			660			991		μm								
Responsivity (Flat Window Package)	$R_\lambda$	λ=850nm			0.50			0.50			0.50			0.50			0.50		A/W								
Dark Current	I <sub>d</sub>	V <sub>R</sub> = 5.0V			0.02	0.80		0.03	0.80		0.06	1.00		0.09	1.50		0.30	2.00	nA								
Capacitance	Cj	$V_{R} = 3.3V$ $V_{R} = 5.0V$			0.9			0.9			2.1			2.8			5.2		-5								
					0.80			0.80			1.8			2.6			4.9		pF								
Rise Time	t <sub>r</sub>				÷					10% to 90%	V <sub>R</sub> = 3.3V		0.75			0.75			1.00			1.10			1.20		
		$R_L = 50\Omega$ λ=850nm	V <sub>R</sub> = 5.0V		0.60			0.60			0.80			0.90			1.00		ns								
Max. Reverse Voltage						20			20			20			20			20	V								
NEP					5.95E -15			6.19E -15			8.76E -15			1.07E -14			1.96E -14		W/√Hz								

Large Active Area and High Speed Silicon Photodiodes

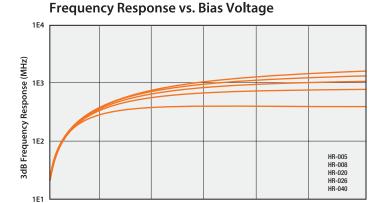
Typical Capacitance vs. Reverse Bias







Pin Circle Diameter = 0.100 (2.54)

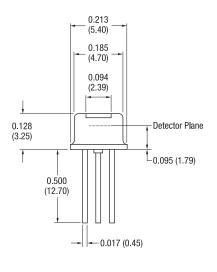


10

15

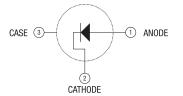
5

0



Reverse Voltage (V)





Pin Circle Diameter = 0.100 (2.54)

## Notes:

- All units in inches (mm).
- All tolerances: 0.005 (0.125).
- Please specify when ordering the flat window or lens cap devices.
- The flat window devices have broadband AR coatings centered at 850nm.
- The thickness of the flat window=0.008 (0.21).